

## ABSTRACT OF THE DISCLOSURE

A gate electrode (1a) is formed on the outer peripheral step portion (1') of a semiconductor substrate (1) so as to face a pressure-contact supporting block (6),  
5 and a convex contacting portion (1g) is formed on a predetermined position on the surface of the gate electrode to contact the pressure contact supporting block. The surface area of the gate electrode ranging from the inner periphery to a position adjacent to the convex contacting  
10 portion, is coated with an insulation film (1d). The convex contacting portion (1g) is formed of a convex portion integral with the gate electrode or formed of another gate electrode (1a').